Number		Search Text	DB	
-	44910	Semi Conductor add	1 28	Time stamp
		semiconductor adj substrate	USPAT	2001/10/10
-	85	(semiconductor adj substrate) and		2001/10/19 11:50
			USPAT	2001/10/18
-	37	((Semiconductor add	1	13:48
			USPAT	2001/10/18
_				13:49
	11	I I I I SCHULCOHOHOLON SAS SUB-		
	1 1		USPAT	2001/10/18
_	224			14:05
	224	("438/697").CCLS.	17000-	
_	26	11"129 (607")	USPAT	2001/10/18
		(("438/697").CCLS.) and (laser or lasers	USPAT	14:08
-	1 1	111"438/603")	OSPAI	2001/10/18
	- 1	((("438/697").CCLS.) and (laser or lasers)) and (option)	USPAT	14:12
•	1		001711	2001/10/18
		(("438/697").CCLS.) and (laser adj	USPAT	2001/10/18
	1426	laser adj annealing		14:16
	1	-	USPAT	2001/10/18
	7	(laser adj annealing) and (optical adj		14:16
	_ 1	mask)	USPAT	2001/10/18
	7	((laser adj annealing) and (optical adj	1.	14:16
	1405	mask)) and (insulat\$3 or dielectric)	USPAT	2001/10/18
{				14:17
			USPAT	2001/10/19
	4/6	((laser adj annealing) or (laser adj	HCDDM	10:27
1			USPAT	2001/10/19
1	((\\+asel dul annealing\ a= /1	USPAT	10:29
			OSFAI	2001/10/19
j	1 \			10:29
ł	c	(((laser adj annealing) or (laser adj	USPAT	2001/10/19
1				10:30
	à	insulating or dielectric)) and amorphous	į	10.30
		nd (single adj crystalline) and morphous monocrystalline)		•
	1 ("5643826").PN.	1	
1	j		USPAT	2001/10/19
	1 (("5643826").PN.) and laser		11:50
	ł		USPAT	2001/10/19
1	1 ('	'5620910").PN.	,,,,,,	12:01
	1 / (/ U.C. CO. O. O	USPAT	2001/10/19
	1 ((("5620910").PN.) and laser	USPAT	12:01
•	l l		USPAI	2001/10/19 .
	1) 1	("5620910").PN.) and laser) and ignment	USPAT	12:01
-	,	- 41 THICTIC	ODIAL	2001/10/19 12:09
ĺ	1	ystal\$ and laser and (alignment adj rk)	USPAT	2001/10/19
				12:14
1		rystal\$ and laser and (alignment adj rk)) and (amorphous adj silicon) and	USPAT	2001/10/19
1				12:15
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			USPAT	2001/10/19
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}			USPAT	2001/10/19
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1	0 1 ((C	rystal\$ and laser and (alignment adj	USPAT	2001/10/55
			OPENI	2001/10/19
				12:16
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			JSPAT	2001/10/19
1		k)) and (amorphous adj silicon) and ystalline adj silicon)) and (laser adj	-	12:16
i	1 1 2	eal)		

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	((Crystal\$ and laser and (alignment adj mark)) and (amorphous adj silicon) and (crystalline adj silicon)) and (laser adj	USPAT	2001/10/24 11:02
5	aimeary)	USPAT;	2001/10/24 11:03
5	((Crystal\$ and laser and (alignment adj mark)) and (amorphous adj silicon) and (crystalline adj silicon)) and (laser adj anneal\$)	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2001/10/24 11:07
4527	(thin adj film adj resistor\$2)	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2001/10/24 11:08
94	((thin adj film adj resistor\$2)) and amorphous and ((single adj crystalline) or monocrystalline or single-crystalline or crystalline)	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2001/10/24 11:38
	(("5569610") or ("5543352") or ("0553416") or ("5531182") or ("5529937") or ("5508533") or ("5501989") or ("5488000") or ("5481121") or ("54037722") or ("5289030") or ("5278093") or ("5275851") or ("5147826") or ("4309223") or ("4068020") or ("3783049")).PN.	IBM TDB USPAT	2001/10/24 11:40